

HF/VHF power transistor

BLW76

Description:

N-P-N silicon planar epitaxial transistor intended for use in class-AB or class-B operated high power transmitters in the HF and VHF bands. The transistor presents excellent performance as a linear amplifier in the HF band. It is resistance stabilized and is guaranteed to withstand severe load mismatch conditions. Transistors are delivered in matched hFE groups.

Features:

SOT121B package. The transistor has a 1/2" flange envelope with a ceramic cap. All leads are isolated from the flange.

Data:

MODE OF OPERATION	V _{CE} V	I _{C(zs)} A	f MHz	P _L W	G _p dB	η %	d ₃ dB
s.s.b. (class-AB)	28	0,05	1,6 – 28	8 – 80 (P.E.P.)	> 13	> 35 ⁽¹⁾	< -30
c.w. (class-B)	28	–	108	80	typ. 7,9	typ. 70	–

Drawings:

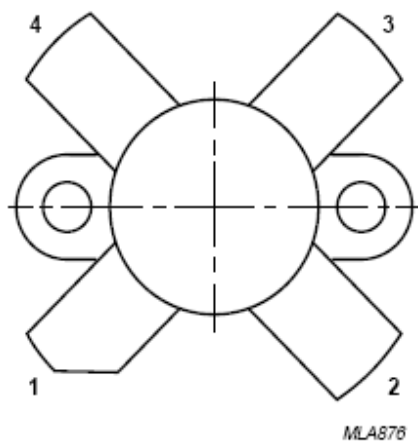
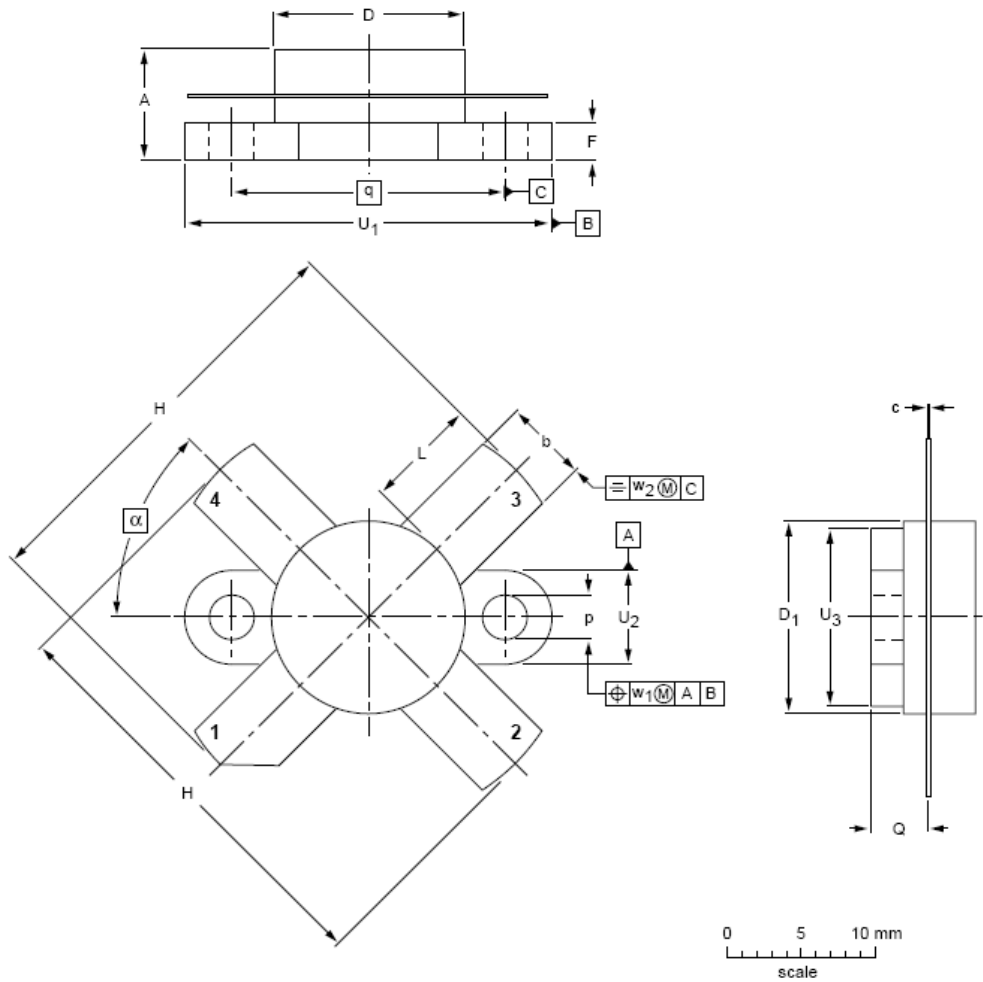


Fig.1 Simplified outline. SOT121B.

PINNING - SOT121B.

PIN	DESCRIPTION
1	collector
2	emitter
3	base
4	emitter



DIMENSIONS (millimetre dimensions are derived from the original inch dimensions)

UNIT	A	b	c	D	D ₁	F	H	L	p	Q	q	U ₁	U ₂	U ₃	w ₁	w ₂	α
mm	7.27 6.17	5.82 5.56	0.16 0.10	12.86 12.59	12.83 12.57	2.67 2.41	28.45 25.52	7.93 6.32	3.30 3.05	4.45 3.91	18.42	24.90 24.63	6.48 6.22	12.32 12.06	0.51	1.02	45°
inches	0.286 0.243	0.229 0.219	0.006 0.004	0.506 0.496	0.505 0.495	0.105 0.095	1.120 1.005	0.312 0.249	0.130 0.120	0.175 0.154	0.725	0.98 0.97	0.255 0.245	0.485 0.475	0.02	0.04	